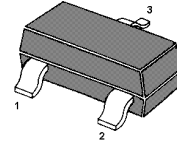


MMBT9015

PNP Silicon Epitaxial Planar Transistors

for switching and AF amplifier applications

As complementary types the NPN transistor
MMBT9014 is recommended.



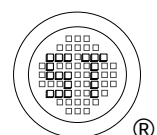
1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	50	V
Collector Emitter Voltage	$-V_{CEO}$	45	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 5\text{ V}$, $-I_C = 1\text{ mA}$ Current Gain Group B C D	h_{FE}	110	220	-
	h_{FE}	200	450	-
	h_{FE}	420	800	-
Collector Base Cutoff Current at $-V_{CB} = 50\text{ V}$	$-I_{CBO}$	-	50	nA
Emitter Base Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	50	nA
Collector Base Breakdown Voltage at $-I_C = 100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	50	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	45	-	V
Emitter Base Breakdown Voltage at $-I_E = 100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$	-	0.65	V
Base Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{BE(sat)}$	-	1	V
Gain Bandwidth Product at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$	f_T	100	-	MHz
Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	7	pF



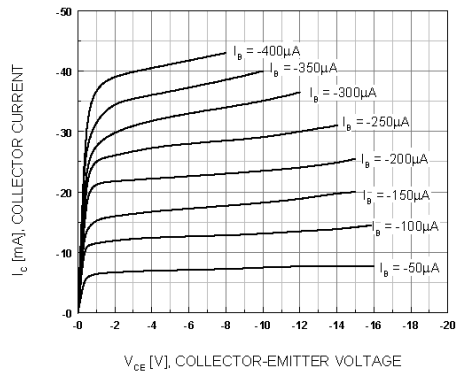


Figure 1. Static Characteristic

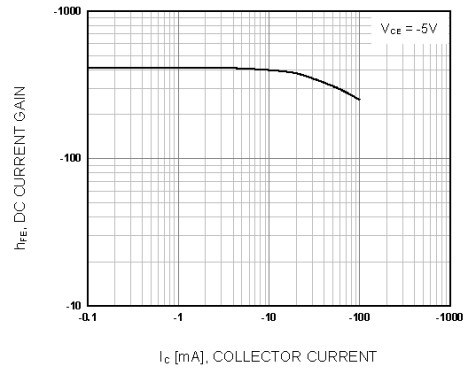


Figure 2. DC current Gain

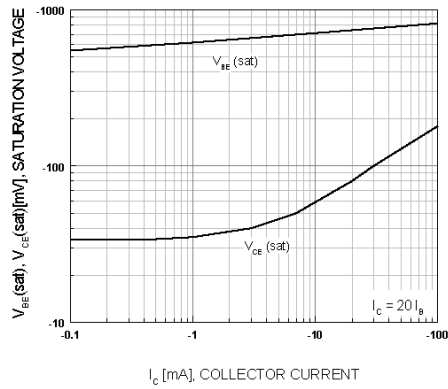


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

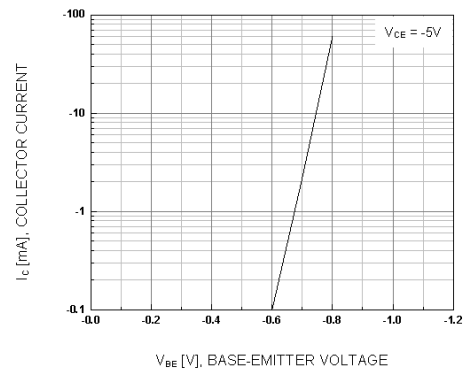


Figure 4. Base-Emitter On Voltage

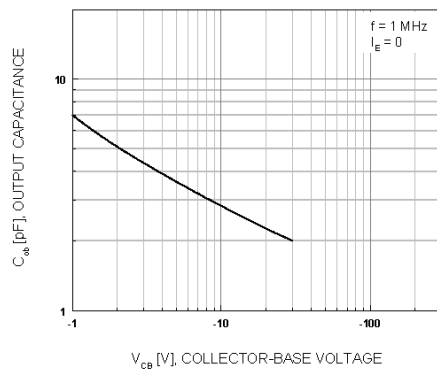


Figure 5. Collector Output Capacitance

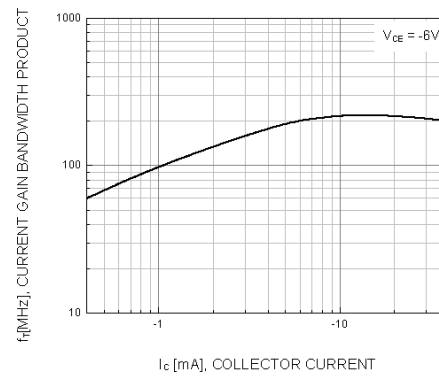


Figure 6. Current Gain Bandwidth Product

